

Features:

- 650V Schottky Diode
- Zero Reverse Recovery Current
- High Frequency Operation
- Positive Temperature Coefficient
- Temperature independent Switching

Benefits:

- Unipolar Rectifier
- Minimal switching loss
- Higher Efficiency
- Low cooling requirement

Symbol	Value	Unit		
$\mathbf{V}_{\mathbf{RRM}}$	650	V		
$I_{F~(Tc=145^{\circ}C)}$	10	A		
$\mathbf{Q}_{\mathbf{C}}$	36	пC		

Outline

Circuit CASE **Applications:** Switch Mode Power Supply Booster diodes in PFC, DC/DC AC/DC converters TO-220-2L

Maximum Ratings

Symbol	Parameter	Value	Unit	Test Conditions
V_R	DC Peak Reverse Voltage	650	V	$T_J = 25^{\circ}C$
V _{RRM}	Repetitive Peak Reverse	650	V	$T_J = 25^{\circ}C$
V _{RSM}	Surge Peak Reverse Voltage	650	V	$T_J = 25^{\circ}C$
$\mathbf{I_F}$	Continuous Forward Current	28 12.5 10	A	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 135^{\circ}{\rm C}$ $T_{\rm C} = 145^{\circ}{\rm C}$
I _{FRM}	Repetitive Peak Forward Surge Current	51 46	A	$T_{\rm C}=25^{\circ}{\rm C},T_{\rm P}=10{\rm ms},{\rm HalfSineWave}$ $T_{\rm C}=125^{\circ}{\rm C},T_{\rm P}=10{\rm ms},{\rm HalfSineWave}$
I _{FSM}	Non-Repetitive Peak Forward Surge Current	67 61	A	$T_{\rm C}=25^{\circ}{\rm C}, T_{\rm P}=10{\rm ms}, {\rm Half~Sine~Wave}$ ${\rm Tc}=125^{\circ}{\rm C}, T_{\rm P}=10{\rm ms}, {\rm Half~Sine~Wave}$
P _D	Power Dissipation	83 27.5	W	$T_{\rm C} = 25^{\circ}{\rm C}$ $T_{\rm C} = 125^{\circ}{\rm C}$
T _{J,max}	Operating Junction Temperature	175	°C	
T _{stg}	Storage Temperature Range	-55 to 175	°C	



Thermal characteristics

Symbol	Parameter	Min.	Тур.	Max.	Unit
$R_{ ext{thJC}}$	Thermal resistance		1.8		°C/W

Electrical Characteristics

Symbol	Parameter	Value		I I \$4	Total Constitutions	
		Min.	Тур.	Max.	Unit	Test Conditions
V _{DC}	DC Blocking Voltage	650			V	$I_R = 100 \mu A, T_J = 25^{\circ} C$
V-	V _F Forward Voltage	1.35	1.6	V	$I_F = 10A, T_J = 25^{\circ}C$	
VF			1.6	1.9	V	$I_F = 10A, T_J = 175^{\circ}C$
I _R	Reverse Current		2	50	μΑ	$V_R = 650V, T_J = 25^{\circ}C$
			15	160		$V_R = 650V, T_J = 175^{\circ}C$
Qc	Total Capacitive Charge		36		пC	$I_F = 10A$, $dI/dt = 300A/\mu s$
						$T_J = 25^{\circ}C, V_R = 400V$
			646			$V_R = 1V, T_J = 25^{\circ}C, f = 1 \text{ MHz}$
C	Total Capacitance		86		pF	$V_R = 200V, T_J = 25^{\circ}C, f = 1 \text{ MHz}$
			82			$V_R = 400V, T_J = 25^{\circ}C, f = 1 \text{ MHz}$

Typical Performance

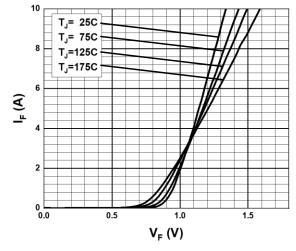


Fig. 1 Forward Characteristics

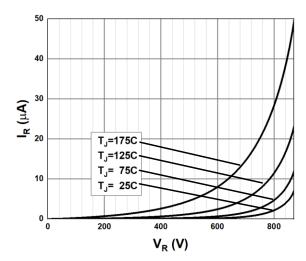


Fig. 2 Reverse Characteristics



Typical Performance

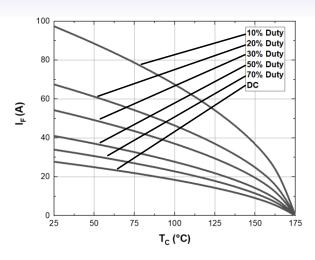


Fig. 3 Current Derating

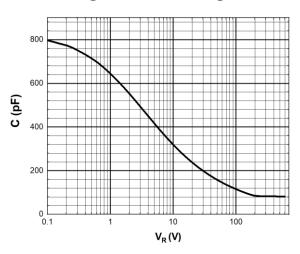


Fig. 5 Capacitance vs. Reverse Voltage

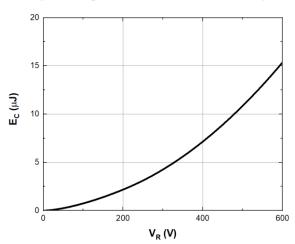


Fig. 7 Capacitance stored Energy

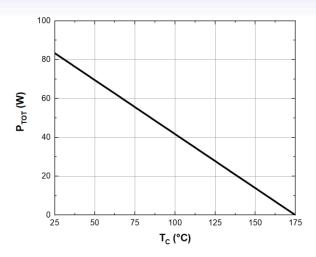


Fig. 4 Power Derating

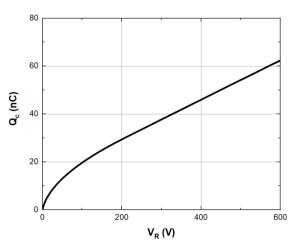
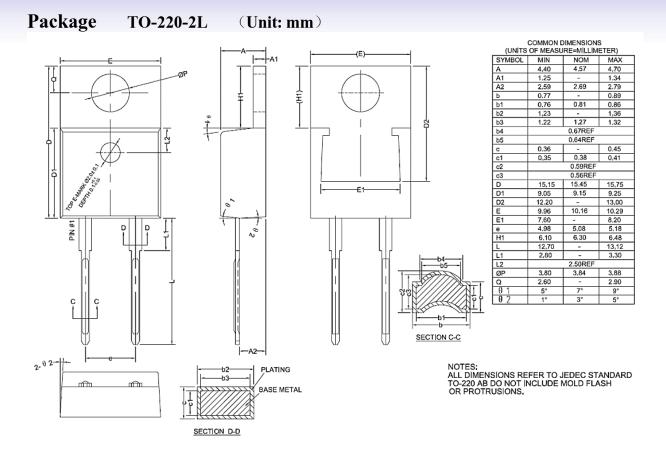


Fig. 6 Recovery Charge vs. Reverse Voltage

S3D065V010A, Rev. 1.0





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5601 W SLAUSON AVE 190 CULVER CITY, CA 90230 WWW.AZPE.COM

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